

FQPF12N60C

N-Channel QFET® MOSFET

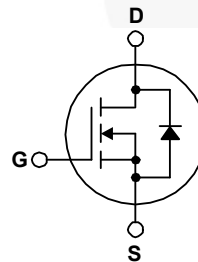
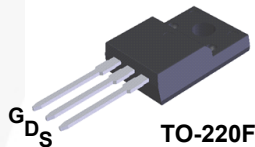
600 V, 12 A, 650 mΩ

Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficient switched mode power supplies, active power factor correction, electronic lamp ballast based on half bridge topology.

Features

- 12 A, 600 V, $R_{DS(on)} = 650 \text{ m}\Omega$ (Max.) @ $V_{GS} = 10 \text{ V}$, $I_D = 6 \text{ A}$
- Low Gate Charge (Typ. 48 nC)
- Low Crss (Typ. 21 pF)
- 100% Avalanche Tested



Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	FQPF12N60C / FQPF12N60CT	Unit
V_{DSS}	Drain-Source Voltage	600	V
I_D	Drain Current	- Continuous ($T_C = 25^\circ\text{C}$)	12*
		- Continuous ($T_C = 100^\circ\text{C}$)	7.4*
I_{DM}	Drain Current - Pulsed (Note 1)	48*	A
V_{GSS}	Gate-Source voltage	± 30	V
E_{AS}	Single Pulsed Avalanche Energy (Note 2)	870	mJ
I_{AR}	Avalanche Current (Note 1)	12	A
E_{AR}	Repetitive Avalanche Energy (Note 1)	22.5	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	4.5	V/ns
P_D	Power Dissipation ($T_C = 25^\circ\text{C}$)	51	W
		- Derate above 25°C	0.41
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$
T_L	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds	300	$^\circ\text{C}$

*Drain current limited by maximum junction temperature

Thermal Characteristics

Symbol	Parameter	FQPF12N60C / FQPF12N60CT	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	2.43	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	$^\circ\text{C}/\text{W}$

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQPF12N60C	FQPF12N60C	TO-220F	Tube	N/A	N/A	50 units
FQPF12N60CT	FQPF12N60CT	TO-220F	Tube	N/A	N/A	50 units

Electrical Characteristics T_C = 25°C unless otherwise noted.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Off Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0 V, I _D = 250 μA, T _J = 25°C	600	--	--	V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 250 μA, Referenced to 25°C	--	0.5	--	V/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 600 V, V _{GS} = 0 V V _{DS} = 480 V, T _C = 125°	--	--	1 10	μA μA
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 30 V, V _{DS} = 0 V	--	--	100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -30 V, V _{DS} = 0 V	--	--	-100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250 μA	2.0	--	4.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10 V, I _D = 6 A	--	0.53	0.65	Ω
g _{FS}	Forward Transconductance	V _{DS} = 40 V, I _D = 6 A	--	13	--	S
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} = 25 V, V _{GS} = 0 V, f = 1.0 MHz	--	1760	2290	pF
C _{oss}	Output Capacitance		--	182	235	pF
C _{rss}	Reverse Transfer Capacitance		--	21	28	pF
Switching Characteristics						
t _{d(on)}	Turn-On Delay Time	V _{DD} = 300 V, I _D = 12 A R _G = 25 Ω (Note 4)	--	30	70	ns
t _r	Turn-On Rise Time		--	85	180	ns
t _{d(off)}	Turn-Off Delay Time		--	140	280	ns
t _f	Turn-Off Fall Time		--	90	190	ns
Q _g	Total Gate Charge	V _{DS} = 400 V, I _D = 12 A V _{GS} = 10 V (Note 4)	--	48	63	nC
Q _{gs}	Gate-Source Charge		--	8.5	--	nC
Q _{gd}	Gate-Drain Charge		--	21	--	nC
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain-Source Diode Forward Current		--	--	12	A
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	48	A
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0V, I _S = 12 A	--	--	1.4	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0V, I _S = 12 A di _F /dt = 100 A/μs	--	420	--	ns
Q _{rr}	Reverse Recovery Charge		--	4.9	--	μC

NOTES:

1. Repetitive rating; pulse-width limited by maximum junction temperature.
2. L = 11 mH, I_{AS} = 12 A, V_{DD} = 50 V, R_G = 25 Ω, starting T_J = 25°C.
3. I_{SD} ≤ 12 A, di/dt ≤ 200 A/μs, V_{DD} ≤ BV_{DSS}, starting T_J = 25°C.
4. Essentially independent of operating temperature typical characteristics.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

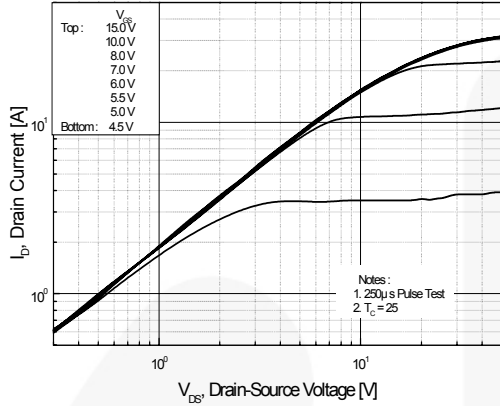


Figure 2. Transfer Characteristics

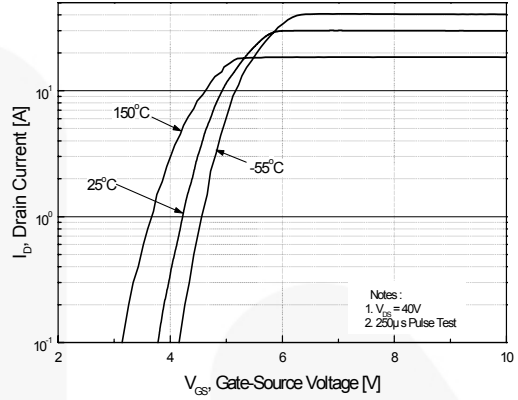


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

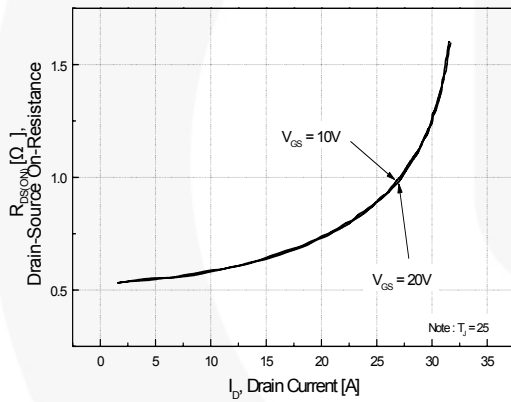


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

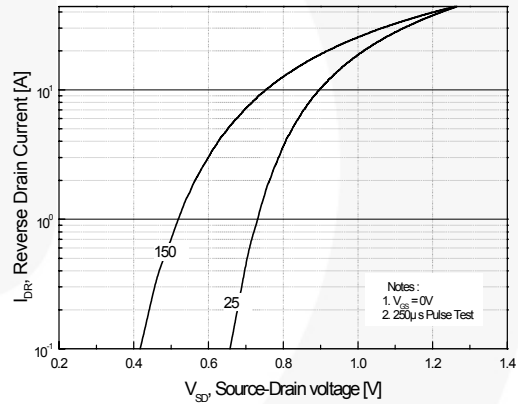


Figure 5. Capacitance Characteristics

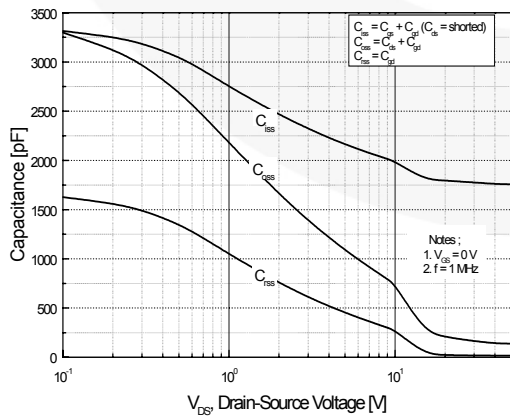
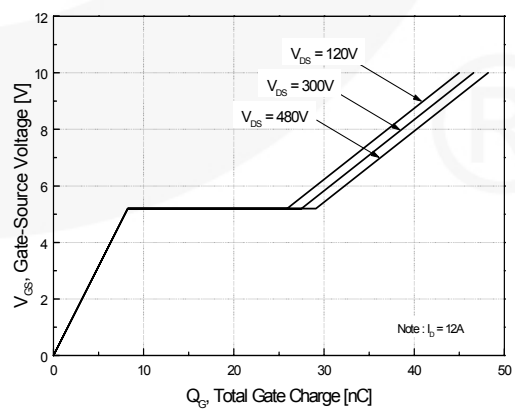


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

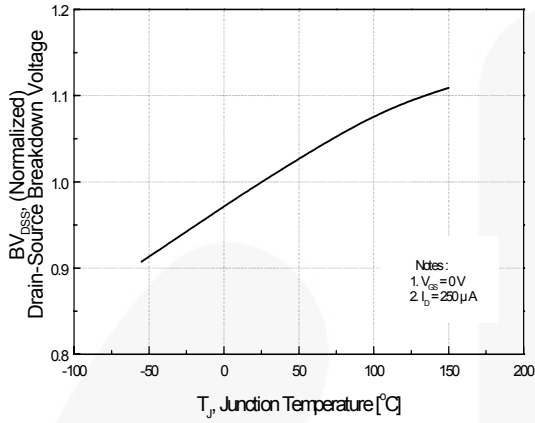


Figure 8. On-Resistance Variation vs. Temperature

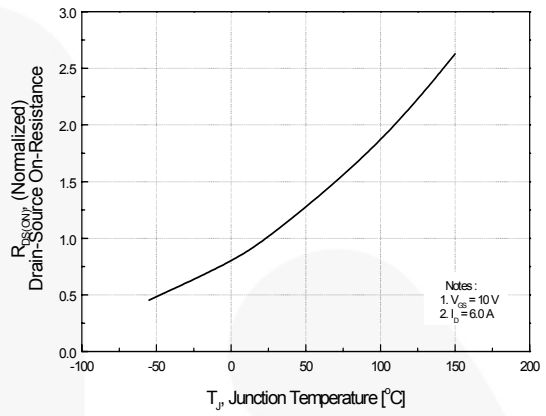


Figure 9. Maximum Safe Operating Area

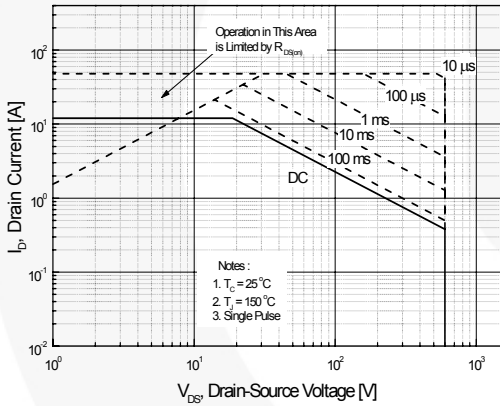


Figure 10. Maximum Drain Current vs. Case Temperature

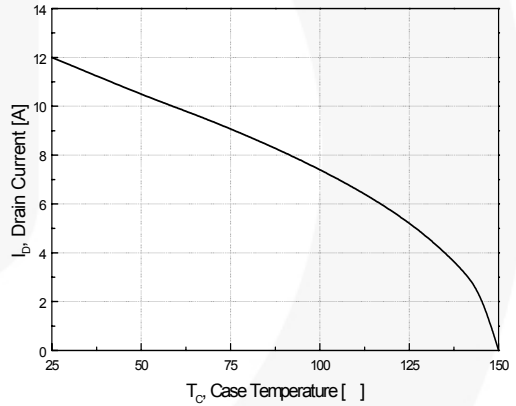
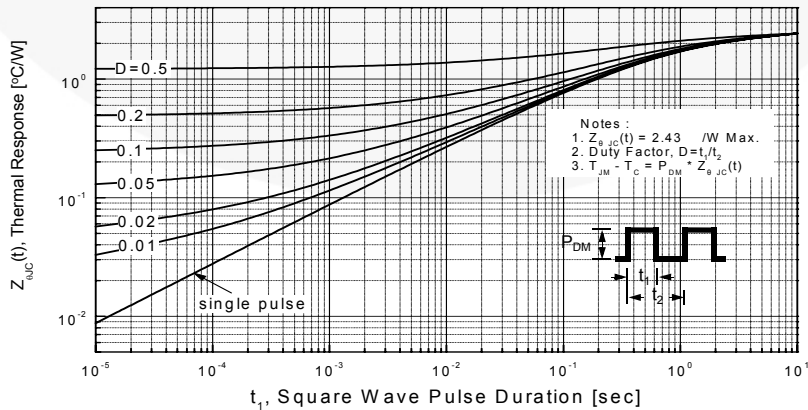


Figure 11. Transient Thermal Response Curve



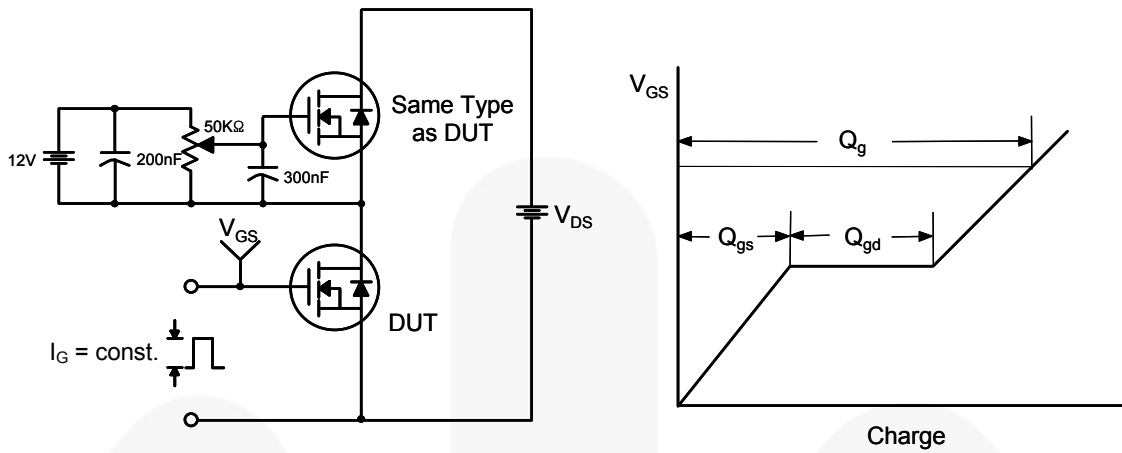


Figure 12. Gate Charge Test Circuit & Waveform

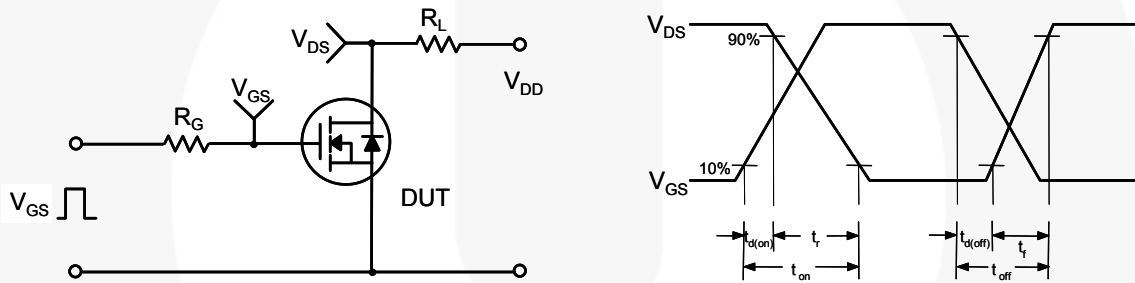


Figure 13. Resistive Switching Test Circuit & Waveforms

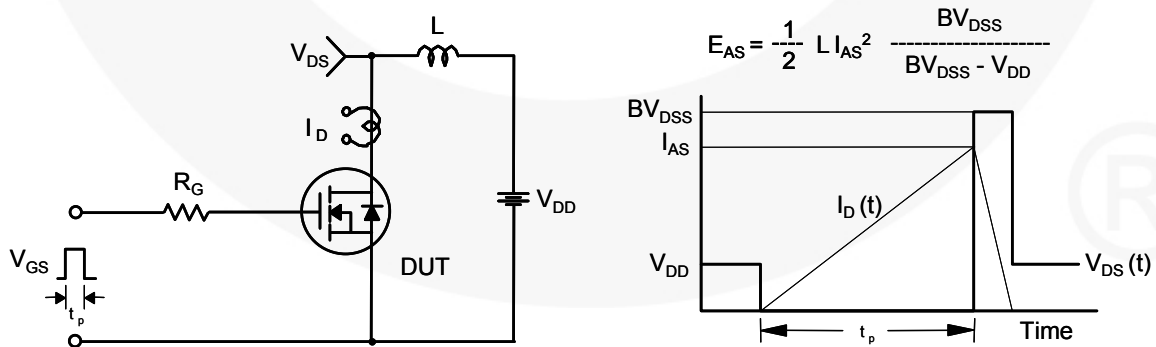


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

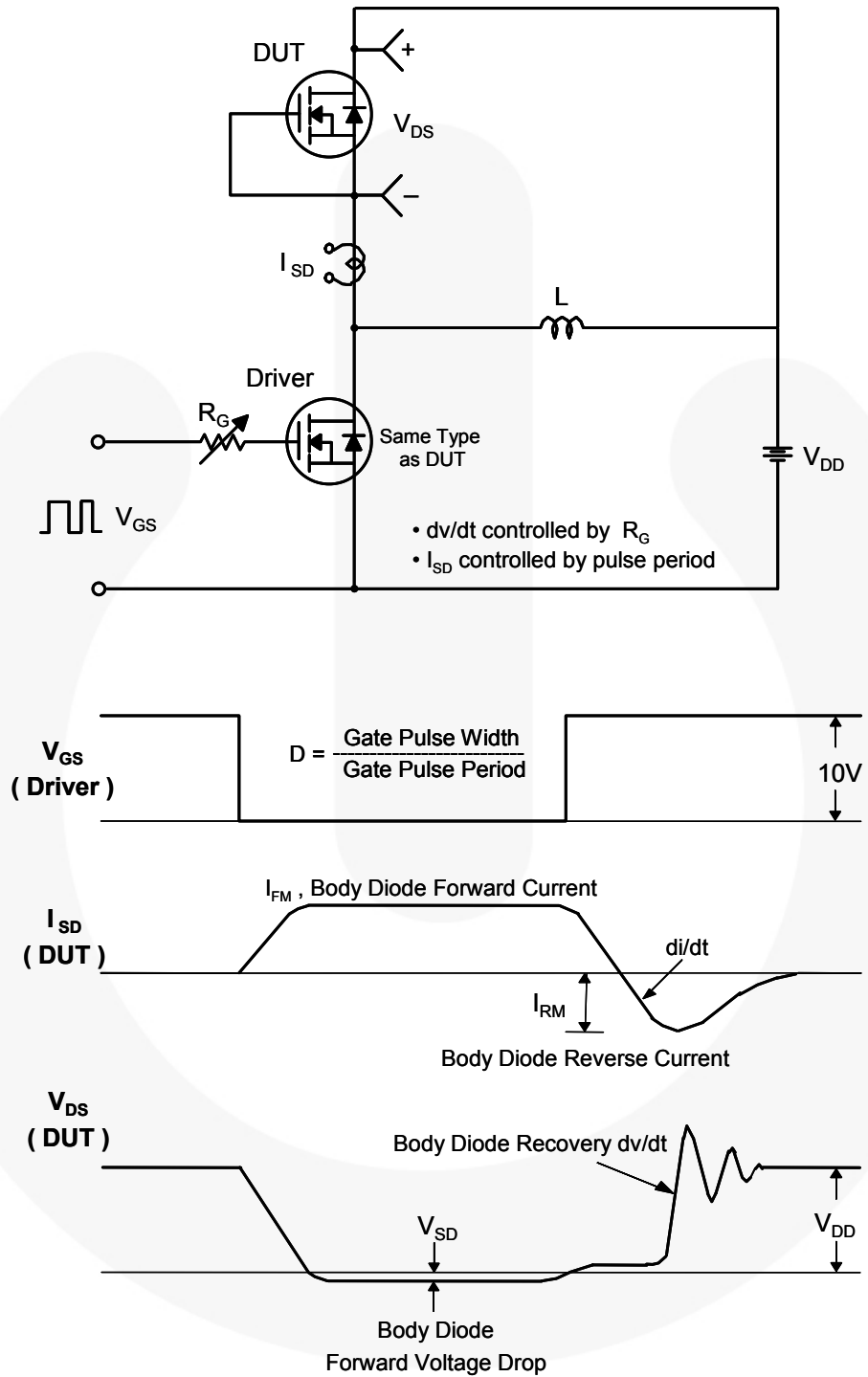


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechanical Dimensions



NOTES:

- A. EXCEPT WHERE NOTED CONFORMS TO EIAJ SC91A.
- B. DOES NOT COMPLY EIAJ STD. VALUE.
- C. ALL DIMENSIONS ARE IN MILLIMETERS.
- D. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR PROTRUSIONS.
- E. DIMENSION AND TOLERANCE AS PER ASME Y14.5-1994.
- F. OPTION 1 - WITH SUPPORT PIN HOLE.
OPTION 2 - NO SUPPORT PIN HOLE.
- G. DRAWING FILE NAME: TO220M03REV3

Figure 16. TO220, Molded, 3-Lead, Full Pack, EIAJ SC91, Straight Lead

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Rev. I66